

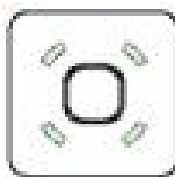
### CE08U15P0S1

### 1-channel ultra low capacitance ESD diode

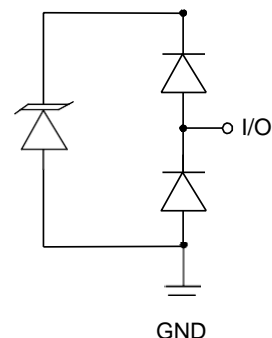
#### Wafer Information

Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um $\pm$ 10um
Die Size (with scribe lane)	206um x 206um
Bond Pad Opening	72um x 72um
Scribe Lane Width	50um
Gross Die Per Wafer	357,000
Top Metal (for wire bond)	4 $\mu$ m AlSiCu
Backside Metal (for die bond)	Sn

#### Die Appearance



#### Circuit Diagram



- Complies with IEC 61000-4-2 standards:  
Contact discharge:  $\pm 8$ kV

#### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Operating Temperature Range	$T_J$	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

#### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

### CE08U15P0S1

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.5			V	$I_T = 1\text{mA}$
Reverse Leakage Current	$I_R$			100	nA	VRWM = 15V
Forward voltage	$V_F$			1.2	V	$I_F = 15\text{mA}$
Clamping Voltage	VC			28	V	$I_{PP} = 1\text{A}$ (8 x 20 $\mu$ s pulse)
Clamping Voltage	VC			29	V	$I_{PP} = 1.4\text{A}$ (8 x 20 $\mu$ s pulse)
Junction Capacitance	$C_J$		0.45	0.60	pF	VR = 0V, f = 1MHz

**Note:** Electrical parameters are only for die, performance may alter after assembly.